Vishay Semiconductors

Thyristor, Surface Mount, Phase Control SCR, 16 A



D²PAK

PRODUCT SUMMARY				
Package TO-263AB (D ² PAK)				
Diode variation	Single SCR			
I _{T(AV)}	16 A			
V _{DRM} /V _{RRM}	800 V, 1200 V			
V _{TM}	1.25 V			
I _{GT}	45 mA			
TJ	- 40 to 125 °C			

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed qualified and according JEDEC-JESD47
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Input rectification (soft start)
- · Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	PLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE					
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5				
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A			
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0				

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	16	А			
I _{RMS}		25	A			
V _{RRM} /V _{DRM}		800 to 1200	V			
I _{TSM}		350	A			
V _T	16 A, T _J = 25 °C	1.25	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
TJ		- 40 to 125	°C			

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} ∕I _{DRM} , AT 125 °C mA			
VS-25TTS08SPbF	800	800	10			
VS-25TTS12SPbF	1200	1200	10			







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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES		
FARAMETER	STNIDUL	STMBOL TEST CONDITIONS		TYP.	MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	conduction half sine wave	1	6		
Maximum RMS on-state current	I _{RMS}			2	25	А	
Maximum peak, one-cycle,		10 ms sine pulse,	rated V _{RRM} applied	3	00	A	
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	3	50		
Maximum I ² t for fusing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	450		A ² s	
Maximum -t for fusing	141	10 ms sine pulse,	no voltage reapplied	630		A-5	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 10 m	is, no voltage reapplied	63	800	A²√s	
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C		1.	25	V	
On-state slope resistance	r _t	T 105 %O		12	2.0	mΩ	
Threshold voltage	V _{T(TO)}	1j = 125 C	T _J = 125 °C		.0	V	
Maximum reverse and direct leakage current	1 /1	T _J = 25 °C	V_{-} Deted V_{-} $\Lambda/$	0	.5		
Maximum reverse and direct leakage current	IRM/IDM	I_{RM}/I_{DM} $T_{J} = 125 \ ^{\circ}C$ $V_{R} = Rated V_{RRM}/V_{DRM}$		1	0		
Holding current	Ι _Η	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	-	150	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$		2	00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max., linear$	ar to 80 %, $V_{DRM} = R_g - k = Open$	5	00	V/µs	
Maximum rate of rise of turned-on current	dl/dt			1	50	A∕µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	60		
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45	mA	
		Anode supply = 6 V, resistive load, T_J = 125 °C	20		
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	2.5		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V	
Maximum DC gate voltage not to trigger	V _{GD}				
Maximum DC gate current not to trigger	I _{GD}	$T_{\rm J} = 125 ^{\circ}\text{C}, V_{\text{DRM}} = \text{Rated value}$ 2.		mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9		
Typical reverse recovery time	t _{rr}	T 105 %C	4	μs	
Typical turn-off time	tq	T _J = 125 °C	110		

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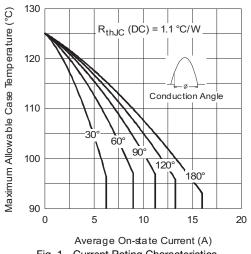
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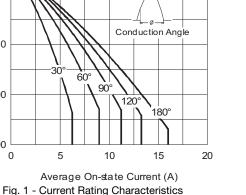
THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C	
Soldering temperature	Τ _S	For 10 s (1.6 mm from case)	260		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W	
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	0/11	
Approximate weight			2	g	
Approximate weight			0.07	oz.	
Marking device		Case style D ² PAK (SMD-220)	25TT	S08S	
		Case signe D-FAR (SIVID-220)	25TT	S12S	

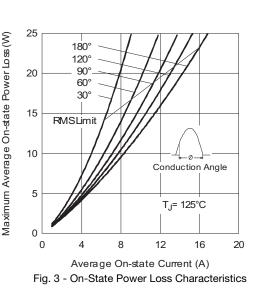
Note

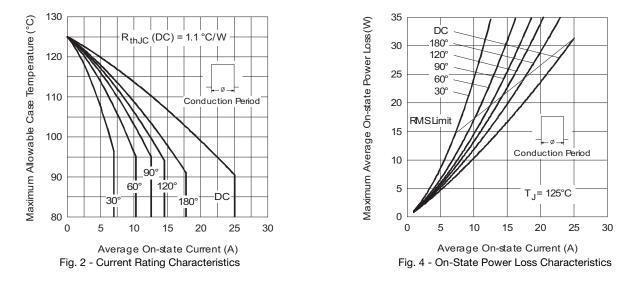
(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W

For recommended footprint and soldering techniques refer to application note #AN-994







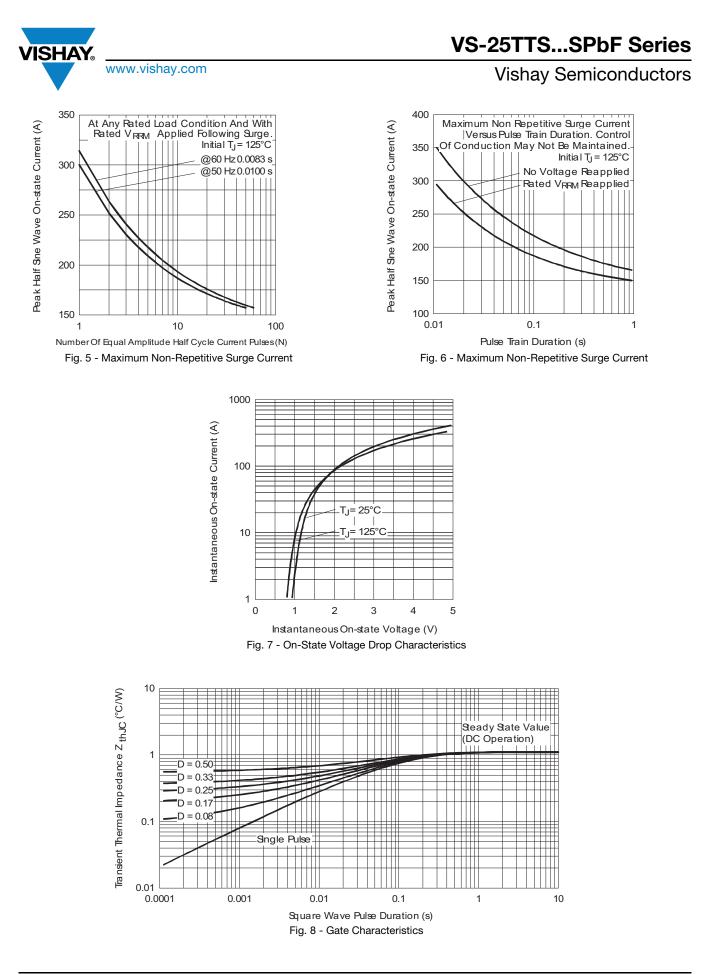


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VS-25TTS...SPbF Series

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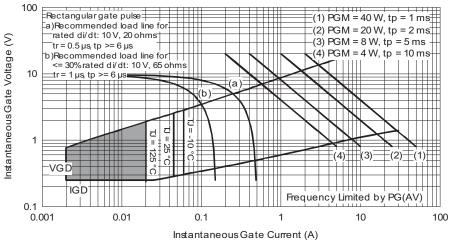


Fig. 9 - Thermal Impedance ZthJC Characteristics

ORDERING INFORMATION TABLE

www.vishay.com

Device code	VS-	25	т	т	S	12	S	TRL	PbF	
	1	2	3	4	5	6	7	8	9	
	1 -	- Visl	nay Sen	niconduc	ctors pro	oduct				
	2 -	- Cur	rent rati	ng (25 =	= 25 A)					
	3 -		uit conf Single t	iguratior hyristor	ו:					
	4 -		kage: TO-220	AC						
	5 -	- Тур	e of silio		erv rect	ifier			08 = 8	800 V
	6 -			ng: Volt) = V _{RRI}	M		200 V
	7 -	- S =	TO-220) D ² PAK	(SMD-	220) ve	rsion			
	8 -	• TF		ube be and re pe and r			,			
	9 -	· PbF	= Leac	l (Pb)-fre	ee					

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-25TTS08SPbF	50	1000	Antistatic plastic tubes				
VS-25TTS08STRRPbF	800	800	13" diameter reel				
VS-25TTS08STRLPbF	800	800	13" diameter reel				
VS-25TTS12SPbF	50	1000	Antistatic plastic tubes				
VS-25TTS12STRRPbF	800	800	13" diameter reel				
VS-25TTS12STRLPbF	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95046				
Part marking information	www.vishay.com/doc?95054			
Packaging information	www.vishay.com/doc?95032			

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Outline Dimensions

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D²PAK



Conforms to JEDEC outline D²PAK (SMD-220) в Pad layout (2)(3)A 11.00 MIN.-(E) F (0.43)ŧ (3) L1 4 (|(0.38)^{MIN.} (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З 0.15)^{0.01} Ľ L2 Ĥ ţ В В 2.32 MIN. (0.08) 2.64 (0.103) 2.41 (0.096) (3)Г 2 x b2 С View A - A 2 x h // ± 0.004 M B ⊕ 0.010 M A M B Base Plating (4) Metal 2 x e Н b1, b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 A1 Lead tip (b, b2) Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A" 3. - Anode

Rotated 90 °CW Scale: 8:1

SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES	STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

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DIMENSIONS in millimeters and inches



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